

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Previously Presented) A film-forming apparatus comprising:
  - a container to be depressurized;
  - a depressurizing mechanism coupled to said container for depressurizing an inside of said container;
  - a film-forming material supply apparatus coupled to said container for supplying a film-forming material or a film-forming material precursor into said container; and
  - a substrate-placing portion located inside said container for placing a substrate on which the film-forming material is deposited,
    - wherein said film-forming material supply apparatus comprises:
      - an evaporation mechanism, located outside said container, for evaporating said film-forming material or said film-forming material precursor to produce an evaporated film-forming material or an evaporated film-forming material precursor; and
      - directing means coupled to said evaporation mechanism and said container and for using a transport gas to direct the evaporated film-forming material or the evaporated film-forming material precursor towards said substrate that is placed on said substrate-placing portion.
2. (Previously Presented) The film-forming apparatus according to claim 1, wherein said directing means comprises a transport gas-supplying mechanism for supplying said transport gas to transport the evaporated film-forming material or the evaporated film-forming material precursor to a surface of said substrate.
3. (Previously Presented) The film-forming apparatus according to claim 1, wherein said film-forming material or said film-forming material precursor has an evaporation

temperature at which said film-forming material or said film-forming material precursor is evaporated, said evaporation mechanism comprises a heating mechanism for heating said film-forming material or said film-forming material precursor to a first temperature equal to or higher than said evaporation temperature, and a predetermined portion inside said container is heated to a second temperature exceeding said evaporation temperature.

4. (Previously Presented) The film-forming apparatus according to claim 3, wherein a temperature of said substrate is maintained at a third temperature lower than said evaporation temperature.

5. (Previously Presented) The film-forming apparatus according to claim 3, wherein said first temperature and said second temperature are lower than a temperature at which the evaporated film-forming material or the evaporated film-forming material precursor is decomposed.

6. (Previously Presented) The film-forming apparatus according to claim 3, wherein said second temperature is higher than said first temperature.

7. (Previously Presented) The film-forming apparatus according to claim 3, wherein said second temperature is higher than said first temperature by 20°C or more.

8. (Previously Presented) The film-forming apparatus according to claim 4, wherein said third temperature is equal to or lower than said evaporation temperature.

9. (Previously Presented) The film-forming apparatus according to claim 8, wherein said film-forming material is a material for organic EL and said third temperature is less than 100°C.

10. (Previously Presented) The film-forming apparatus according to claim 3, wherein said predetermined portion is a portion adapted to contact the evaporated film-forming material or the evaporated film-forming material precursor and excluding said substrate and said substrate holding portion.

11. (Previously Presented) The film-forming apparatus according to claim 2, wherein said transport gas-supplying mechanism comprises a portion adapted to introduce said transport gas from the outside into a container holding said film-forming material or said film-forming material precursor and a gas ejection portion having a plurality of small holes and located so as to face said substrate, and said transport gas transports said evaporated film-forming material or said evaporated film-forming material precursor to the surface of said substrate through said gas ejection portion.

12. (Previously Presented) The film-forming apparatus according to claim 2, wherein said transport gas-supplying mechanism comprises a mechanism for supplying said transport gas from the outside so as to contact said evaporated film-forming material or said evaporated film-forming material precursor and a mechanism for ejecting the transport gas containing said evaporated film-forming material or said evaporated film-forming material precursor toward said substrate.

13. (Previously Presented) The film-forming apparatus according to claim 12, wherein said mechanism for ejecting comprises a shower plate or a plate comprised of a porous material.

14. (Previously Presented) The film-forming apparatus according to claim 1, wherein said evaporation mechanism is configured to evaporate said film-forming material or said film-forming material precursor during execution of film formation and to stop evaporation during non-execution of film formation.

15. (Previously Presented) The film-forming apparatus according to claim 1, wherein said depressurizing mechanism maintains the inside of said container at a pressure of 10 mTorr to 0.1 mTorr during execution of film formation.

16. (Previously Presented) The film-forming apparatus according to claim 15, wherein said depressurizing means causes a gas flow in said container to be in a molecular flow region during the execution of film formation and causes a gas flow in said container to be in an intermediate flow region or a viscous flow region at least for a certain period during non-execution of film formation.

17. (Previously Presented) The film-forming apparatus according to claim 12, wherein said transport gas is a xenon (Xe) gas.

18. (Previously Presented) The film-forming apparatus according to claim 2, wherein said transport gas contains an inert gas as a main component.

19. (Previously Presented) The film-forming apparatus according to claim 2, wherein said transport gas contains at least one of nitrogen (N), Xe, Kr, Ar, Ne, or He.

20. (Previously Presented) The film-forming apparatus according to claim 1, wherein said depressurizing mechanism comprises a turbo-molecular pump and a roughing vacuum pump and a portion for supplying an inert gas is provided between said turbo-molecular pump and said roughing vacuum pump.

21. (Withdrawn) A film-forming apparatus coupled to a substrate transfer apparatus, said film-forming apparatus characterized in that an air having a dew point temperature of -80°C or less is supplied to a space inside said substrate transfer apparatus.

22. (Previously Presented) The film-forming apparatus according to claim 1, wherein a pressure in said container is set to a molecular flow region during film formation and to a transition flow region or a viscous flow region during non-film.

23. - 24 (Canceled).

25. (Withdrawn) An apparatus for processing under a depressurized condition, characterized by comprising a container to be depressurized, a primary pump coupled to said container, a secondary pump coupled to an exhaust side of said primary pump, and a process object-introducing door coupled to said container through a gasket, wherein at least said gasket is comprised of a material having a low discharge of an organic gas.

26. (Withdrawn) An apparatus according to claim 25, characterized in that said gasket contains organic compound.

27. (Withdrawn) An apparatus according to claim 25, characterized in that said gasket has been subjected to a step of contacting said gasket with water of 80°C or more.

28. (Withdrawn) An apparatus according to claim 26, characterized in that a main component of said organic compound is a perfluoroelastomer.

29. (Withdrawn) An apparatus according to claim 25, characterized by comprising, in addition to said gasket, a plurality of gaskets adapted to maintain air-tightness of said container, wherein the gasket adapted to maintain the air-tightness at a portion with a low attaching/detaching frequency is comprised of metal.

30. (Withdrawn) An apparatus according to claim 29, characterized in that the gasket adapted to maintain the air-tightness at a portion with a high attaching/detaching frequency contains organic compound.

31. (Withdrawn) An apparatus according to claim 30, characterized in that said gasket containing the organic compound has been subjected to a step of contacting said gasket with water of 80°C or more.

32. (Withdrawn) An apparatus according to claim 30, characterized in that a main component of said organic compound is a perfluoroelastomer.

33. (Withdrawn) A film-forming method for depositing a film of a predetermined material on a substrate in a container, said film-forming method characterized by comprising a step of evaporating a raw material used for forming said film of the predetermined material and a step of transporting the evaporated raw material to a surface of said substrate by the use of a gas.

34. (Withdrawn) A film-forming method according to claim 33, characterized in that said evaporating step comprises a step of heating said raw material to a first temperature equal to or higher than a temperature at which said raw material is evaporated, and a step of heating a predetermined portion inside said container to a second temperature exceeding said temperature at which said raw material is evaporated.

35. (Withdrawn) A film-forming method according to claim 34, characterized in that a temperature of said substrate is maintained at a third temperature lower than said temperature at which said raw material is evaporated.

36. (Withdrawn) A film-forming method according to claim 34, characterized in that said first temperature and said second temperature are lower than a temperature at which the evaporated raw material is decomposed.

37. (Withdrawn) A film-forming method according to claim 36, characterized in that said second temperature is higher than said first temperature.

38. (Withdrawn) A film-forming method according to claim 36, characterized in that said second temperature is higher than said first temperature by 20°C or more.

39. (Withdrawn) A film-forming method according to claim 35, characterized in that said third temperature is equal to or lower than said temperature at which said raw material is evaporated.

40. (Withdrawn) A film-forming method according to claim 35, characterized in that said predetermined material is an organic EL material and said third temperature is less than 100°C.

41. (Withdrawn) A film-forming method according to claim 34, characterized in that said predetermined portion is a portion adapted to contact said evaporated raw material and excluding said substrate.

42. (Withdrawn) A film-forming method according to claim 33, characterized in that said raw material is said predetermined material or a precursor of said predetermined material.

43. (Withdrawn) A film-forming method according to claim 33, characterized by placing said raw material in a heat-resistant container, placing said heat-resistant container in a gas container, introducing said gas into said gas container to transport said evaporated raw material by the use of said gas, and causing said gas to reach the surface of said substrate through a gas ejection portion while transporting said evaporated raw material, wherein said gas ejection portion having a plurality of small holes is provided so as to face said substrate.

44. (Withdrawn) A film-forming method according to claim 33, characterized by maintaining the inside of said container at a pressure of 10 mTorr to 0.1 mTorr during execution of film formation and maintaining the inside of said container at a reduced pressure of 1 Torr or more at least for a certain period during non-execution of film formation.

45. (Withdrawn) A film-forming method according to claim 33, characterized by causing a gas flow in said container to be in a molecular flow region during execution of film formation and causing a gas flow in said container to be in an intermediate flow region or a viscous flow region at least for a certain period during non-execution of film formation.

46. (Withdrawn) A film-forming method according to claim 33, characterized in that said gas is a xenon (Xe) gas.

47. (Withdrawn) A film-forming method according to claim 33, characterized in that said gas contains an inert gas as a main component.

48. (Withdrawn) A film-forming method according to claim 47, characterized in that said inert gas contains at least one of nitrogen (N), Xe, Kr, Ar, Ne, and He.

49. (Withdrawn) A film-forming method according to claim 33, characterized in that said predetermined material is an organic EL element material.

50. (Withdrawn) An organic EL device manufacturing method characterized by comprising a step of forming a film of an organic EL element material by the use of the film-forming method according to claim 33.

51. (Withdrawn) An electronic device manufacturing method characterized by comprising a step of forming a film layer of a predetermined material by the use of the film-forming method according to claim 33.

52. (Withdrawn) An organic EL device having an organic EL layer formed by the use of the film-forming method according to claim 33.

53. (Withdrawn) An electronic device having a layer of a predetermined material formed by the use of the film-forming method according to claim 33.

54. (Previously Presented) The film-forming apparatus according to claim 1, further comprising a heating portion for pre-heating said transport gas before said transport gas comes in contact with said evaporated film-forming material or said evaporated film-forming material precursor.